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PDTD1xxxU series

500 mA, 50 V NPN resistor-equipped transistors

Rev. 1 — 13 May 2014 Product data sheet

1. Product profile

1.1 General description

NPN Resistor-Equipped Transistor (RET) family in a very small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package			PNP complement	Package configuration
	NXP	JEITA	JEDEC		
PDTD113EU	SOT323	SC-70	-	PDTB113EU	very small
PDTD113ZU				PDTB113ZU	
PDTD123EU				PDTB123EU	
PDTD123YU				PDTB123YU	
PDTD143EU				PDTB143EU	
PDTD143XU				PDTB143XU	
PDTD114EU				PDTB114EU	

1.2 Features

- 500 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- ± 10 % resistor ratio tolerance
- AEC-Q101 qualified
- High temperature applications up to 175 °C

1.3 Applications

- IC inputs control
- Cost-saving alternative to BC807 or BC817 series transistors in digital applications
- Switching loads

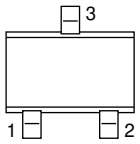
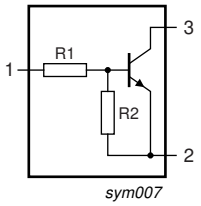
1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I_O	output current		-	-	500	mA
R1	bias resistor 1 (input)					
	PDTD113EU			1		kΩ
	PDTD113ZU			1		kΩ
	PDTD123EU			2.2		kΩ
	PDTD123YU			2.2		kΩ
	PDTD143EU			4.7		kΩ
	PDTD143XU			4.7		kΩ
	PDTD114EU			10		kΩ
R2	bias resistor 2 (base-emitter)					
	PDTD113EU			1		kΩ
	PDTD113ZU			10		kΩ
	PDTD123EU			2.2		kΩ
	PDTD123YU			10		kΩ
	PDTD143EU			4.7		kΩ
	PDTD143XU			10		kΩ
	PDTD114EU			10		kΩ

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	input (base)		
2	GND (emitter)		
3	output (collector)		

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PDTD1xxxU series	SC-70	plastic surface-mounted package; 3 leads	SOT323

4. Marking

Table 5. Marking codes

Type number	Marking code[1]
PDTD113EU	ZP*
PDTD113ZU	ZQ*
PDTD123EU	ZR*
PDTD123YU	ZS*
PDTD143EU	ZT*
PDTD143XU	ZU*
PDTD114EU	ZV*

[1] * = placeholder for manufacturing site code

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector			
	PDTD113EU		-	10	V
	PDTD113ZU		-	5	V
	PDTD123EU		-	10	V
	PDTD123YU		-	5	V
	PDTD143EU		-	10	V
	PDTD143XU		-	7	V
	PDTD114EU		-	10	V
V_I	input voltage				
	PDTD113EU		−10	+10	V
	PDTD113ZU		−5	+10	V
	PDTD123EU		−10	+12	V
	PDTD123YU		−5	+12	V
	PDTD143EU		−10	+30	V
	PDTD143XU		−7	+30	V
	PDTD114EU		−10	+50	V
I_O	output current		-	500	mA

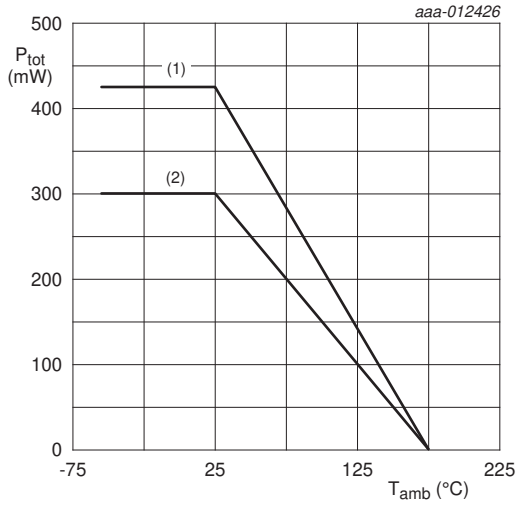
Table 6. Limiting values *...continued*

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	300	mW
			[2]	-	425	mW
T_j	junction temperature			-	175	°C
T_{amb}	ambient temperature			−55	+175	°C
T_{stg}	storage temperature			−55	+175	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.



(1) FR4 PCB, 4-layer copper, standard footprint

(2) FR4 PCB, single-sided copper, standard footprint.

Fig 1. Power derating curves

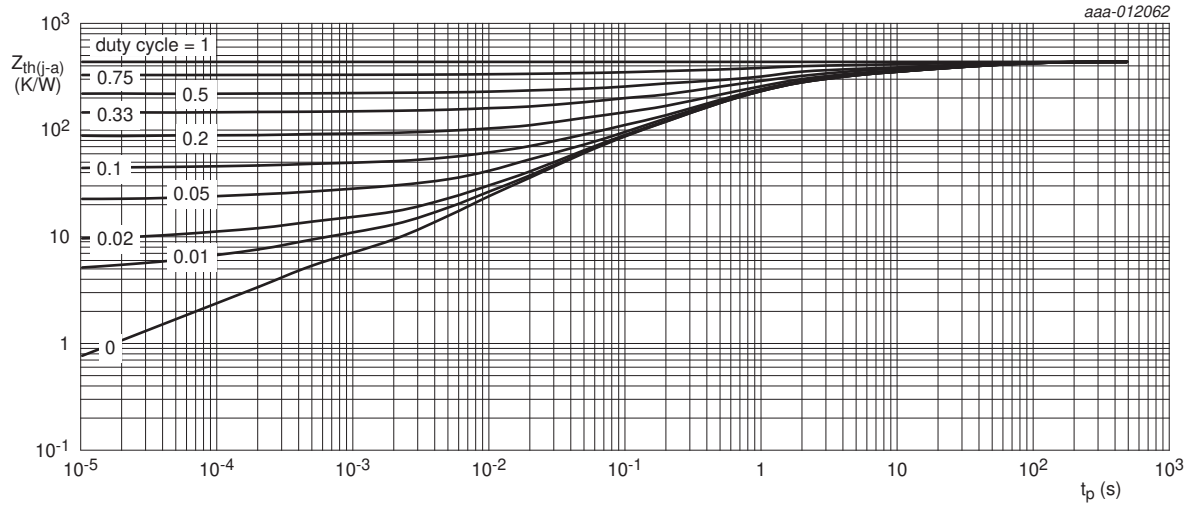
6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W
			[2]	-	-	353	K/W

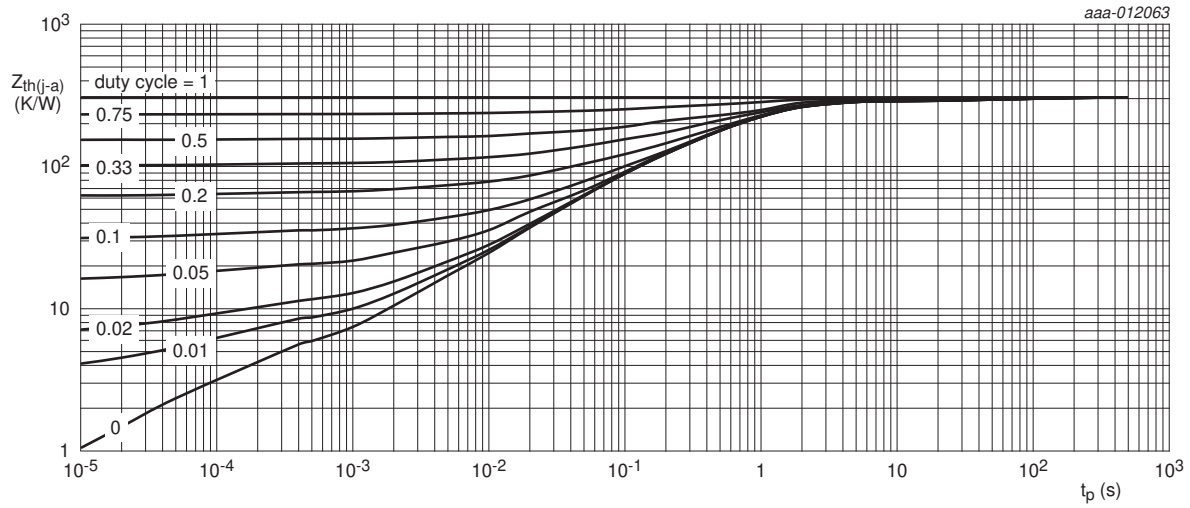
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.



FR4 PCB, single-sided copper, tin-plated and standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT323/SC-70; typical values



FR4 PCB, 4-layer copper, tin-plated and standard footprint.

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT323/SC-70; typical values

7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

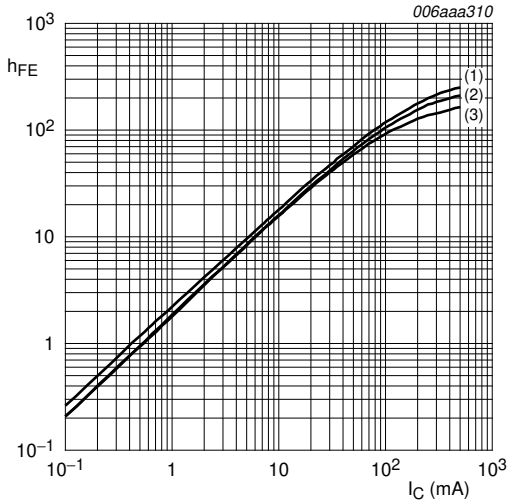
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	V_{CB} = 40 V; I_E = 0 A	-	-	100	nA
		V_{CB} = 50 V; I_E = 0 A	-	-	100	nA
I_{CEO}	collector-emitter cut-off current	V_{CE} = 50 V; I_B = 0 A	-	-	0.5	μA
I_{EBO}	emitter-base cut-off current	V_{EB} = 5 V; I_C = 0 A				
	PDTD113EU		-	-	4.0	mA
	PDTD113ZU		-	-	0.8	mA
	PDTD123EU		-	-	2.0	mA
	PDTD123YU		-	-	0.65	mA
	PDTD143EU		-	-	0.9	mA
	PDTD143XU		-	-	0.6	mA
	PDTD114EU		-	-	0.4	mA
h_{FE}	DC current gain	V_{CE} = 5 V; I_C = 50 mA				
	PDTD113EU		33	-	-	
	PDTD113ZU		70	-	-	
	PDTD123EU		40	-	-	
	PDTD123YU		70	-	-	
	PDTD143EU		60	-	-	
	PDTD143XU		70	-	-	
	PDTD114EU		70	-	-	
V_{CEsat}	collector-emitter saturation voltage	I_C = 50 mA; I_B = 2.5 mA	-	-	100	mV
$V_{I(off)}$	off-state input voltage	V_{CE} = 5 V; I_C = 100 μA				
	PDTD113EU		0.6	1.1	1.5	V
	PDTD113ZU		0.3	0.6	1.0	V
	PDTD123EU		0.6	1.1	1.8	V
	PDTD123YU		0.4	0.6	1.0	V
	PDTD143EU		0.6	0.9	1.5	V
	PDTD143XU		0.5	0.75	1.1	V
	PDTD114EU		0.6	1.0	1.5	V
$V_{I(on)}$	on-state input voltage	V_{CE} = 0.3 V; I_C = 20 mA				
	PDTD113EU		1.0	1.4	1.8	V
	PDTD113ZU		0.4	0.8	1.4	V
	PDTD123EU		1.0	1.5	2.0	V
	PDTD123YU		0.5	1.0	1.4	V
	PDTD143EU		1.0	1.6	2.2	V
	PDTD143XU		1.0	1.25	2.0	V
	PDTD114EU		1.0	1.9	3.0	V

Table 8. Characteristics *...continued*

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R1	bias resistor 1 (input)					
	PDTD113EU		0.7	1.0	1.3	kΩ
	PDTD113ZU		0.7	1.0	1.3	kΩ
	PDTD123EU		1.54	2.2	2.86	kΩ
	PDTD123YU		1.54	2.2	2.86	kΩ
	PDTD143EU		3.3	4.7	6.1	kΩ
	PDTD143XU		3.3	4.7	6.1	kΩ
	PDTD114EU		7.0	10	13	kΩ
R2/R1	bias resistor ratio					
	PDTD113EU		0.9	1.0	1.1	
	PDTD113ZU		9.0	10	11	
	PDTD123EU		0.9	1.0	1.1	
	PDTD123YU		4.1	4.55	5.0	
	PDTD143EU		0.9	1	1.1	
	PDTD143XU		1.91	2.13	2.34	
	PDTD114EU		0.9	1.0	1.1	
C_c	collector capacitance	V_{CB} = 10 V; $I_E = i_e$ = 0 A; f = 1 MHz	-	7	-	pF
f_T	transition frequency	V_{CE} = 5 V; I_C = 50 mA; f = 100 MHz [1]	-	225	-	MHz

[1] Characteristics of built-in transistor.



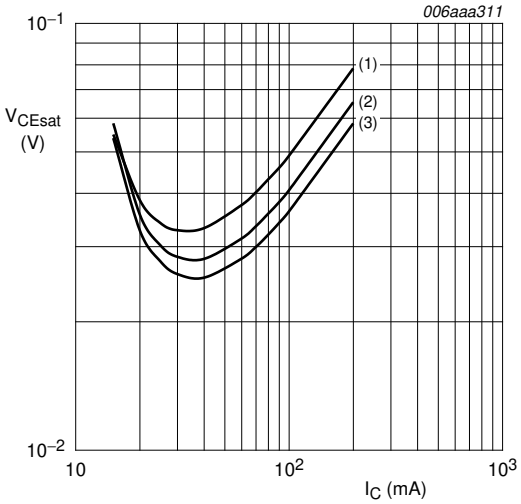
V_{CE} = 5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 4. PDTD113EU: DC current gain as a function of collector current; typical values



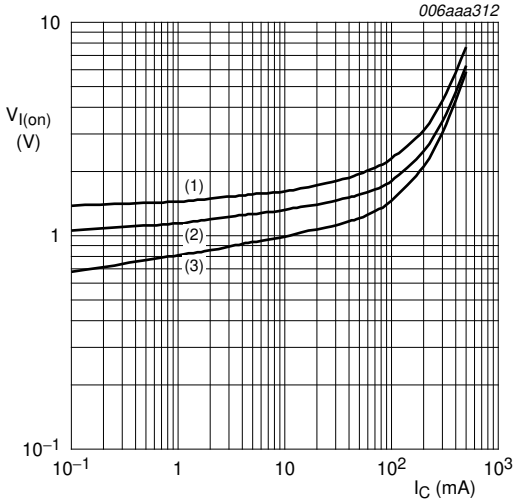
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 5. PDTD113EU: Collector-emitter saturation voltage as a function of collector current; typical values



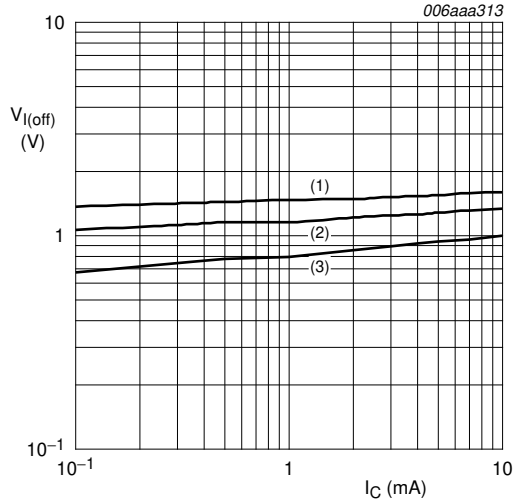
V_{CE} = 0.3 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 6. PDTD113EU: On-state input voltage as a function of collector current; typical values



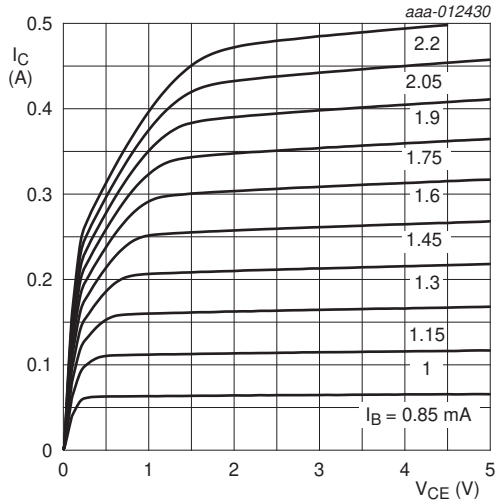
V_{CE} = 5 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

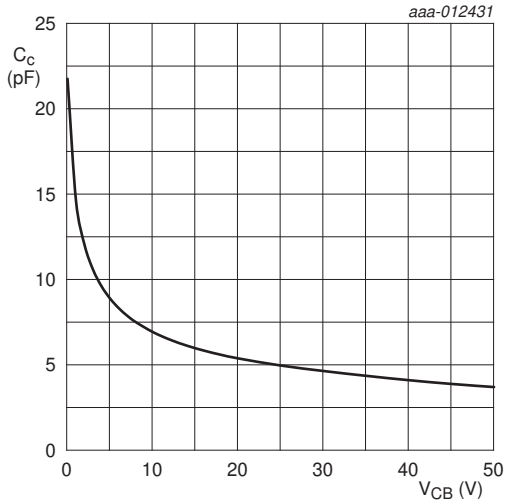
(3) T_{amb} = 100 °C

Fig 7. PDTD113EU: Off-state input voltage as a function of collector current; typical values



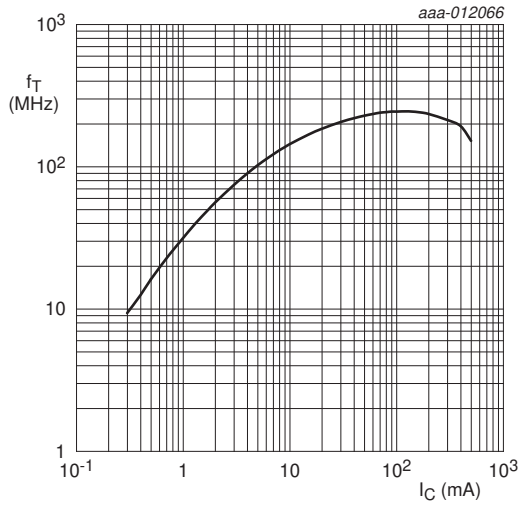
T_{amb} = 25 °C

Fig 8. PDTD113EU: Collector current as a function of collector-emitter voltage; typical values



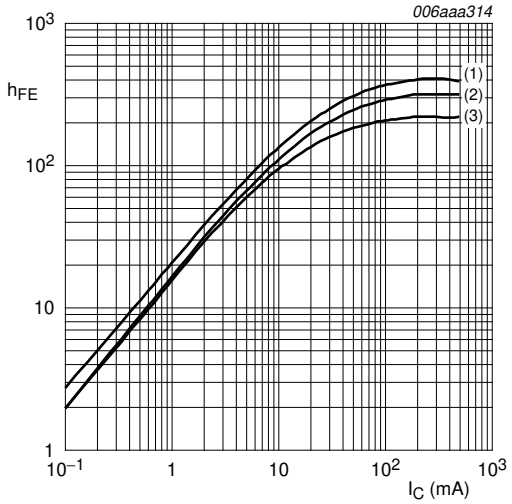
f = 1 MHz; T_{amb} = 25 °C

Fig 9. PDTD113EU: Collector capacitance as a function of collector-base voltage; typical values



V_{CE} = 5 V; T_{amb} = 25 °C

Fig 10. PDTD113EU: Transition frequency as a function of collector current; typical values of built-in transistor



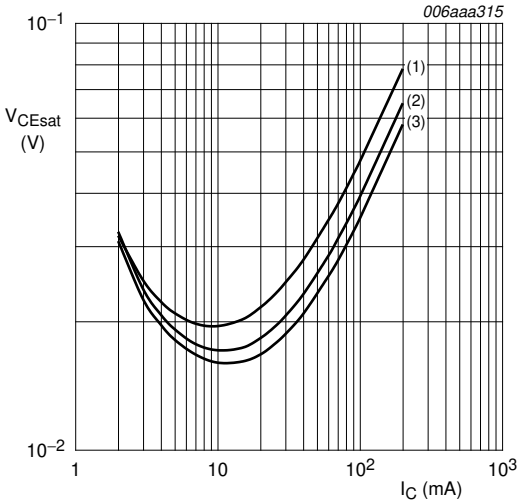
V_{CE} = 5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 11. PDTD113ZU: DC current gain as a function of collector current; typical values



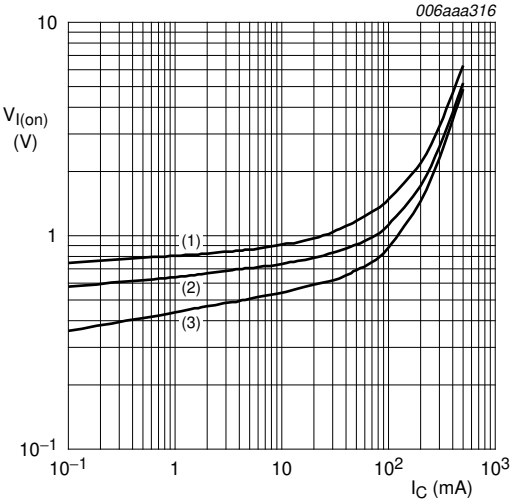
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 12. PDTD113ZU: Collector-emitter saturation voltage as a function of collector current; typical values



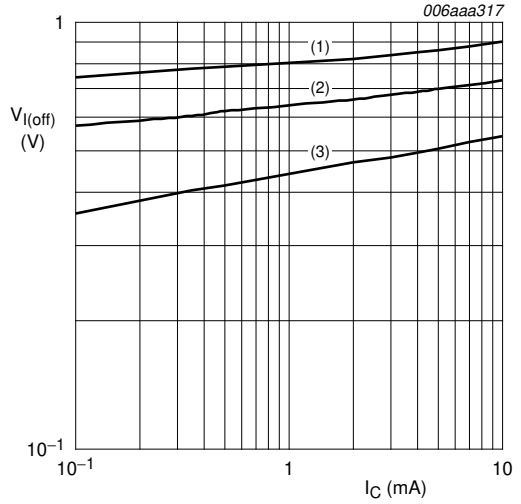
V_{CE} = 0.3 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 13. PDTD113ZU: On-state input voltage as a function of collector current; typical values



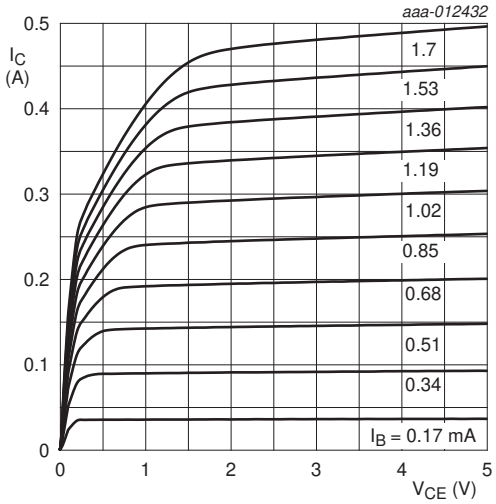
V_{CE} = 5 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

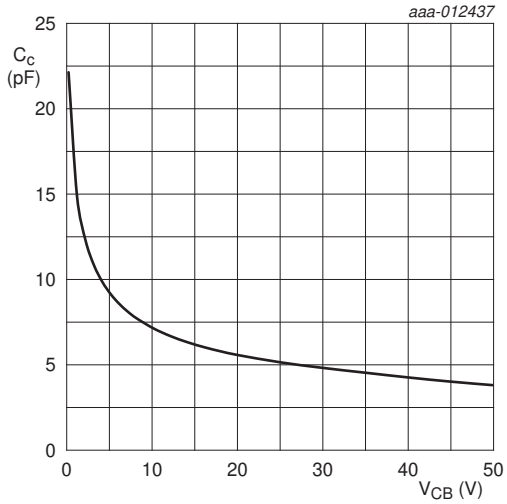
(3) T_{amb} = 100 °C

Fig 14. PDTD113ZU: Off-state input voltage as a function of collector current; typical values



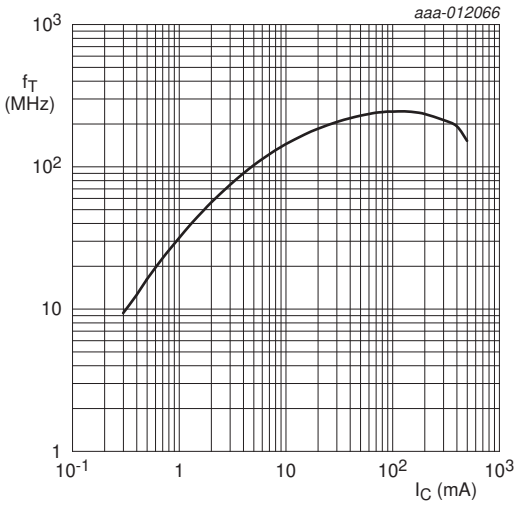
T_{amb} = 25 °C

Fig 15. PDTD113ZU: Collector current as a function of collector-emitter voltage; typical values



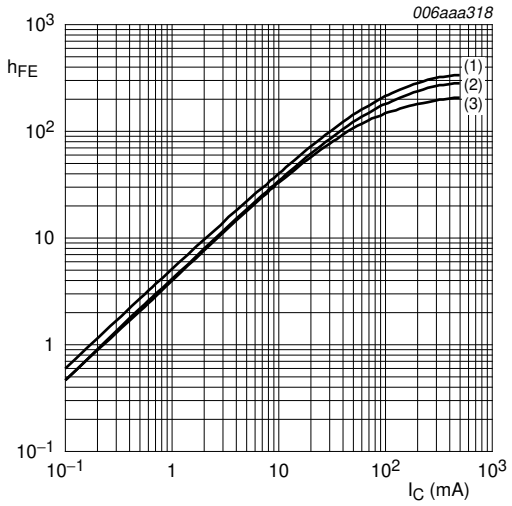
f = 1 MHz; T_{amb} = 25 °C

Fig 16. PDTD113ZU: Collector capacitance as a function of collector-base voltage; typical values



V_{CE} = 5 V; T_{amb} = 25 °C

Fig 17. PDTD113ZU: Transition frequency as a function of collector current; typical values of built-in transistor



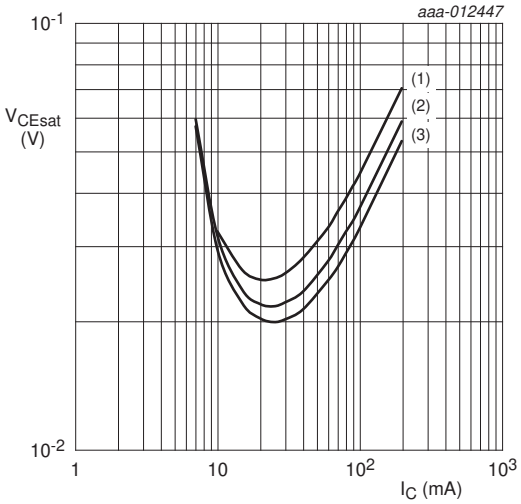
V_{CE} = 5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 18. PDTD123EU: DC current gain as a function of collector current; typical values



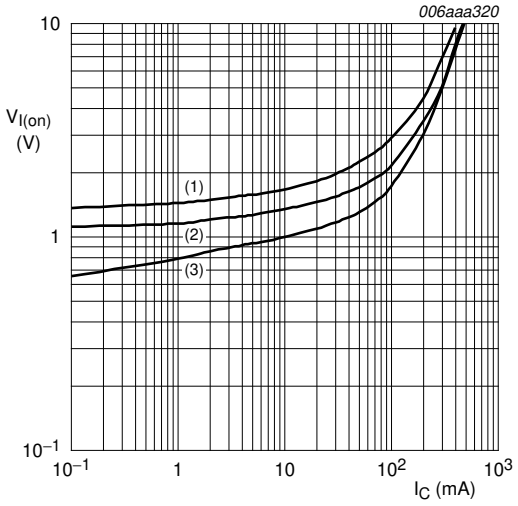
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 19. PDTD123EU: Collector-emitter saturation voltage as a function of collector current; typical values



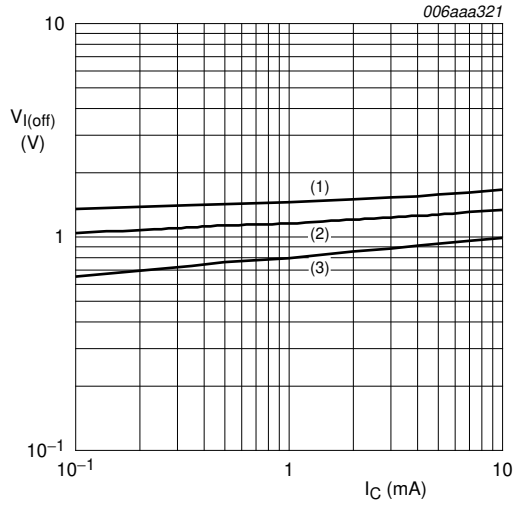
V_{CE} = 0.3 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 20. PDTD123EU: On-state input voltage as a function of collector current; typical values



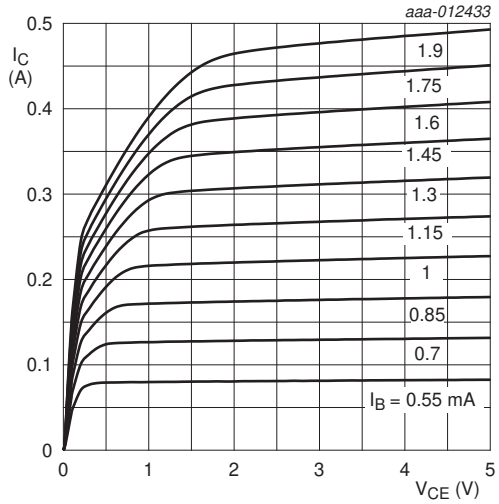
V_{CE} = 5 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

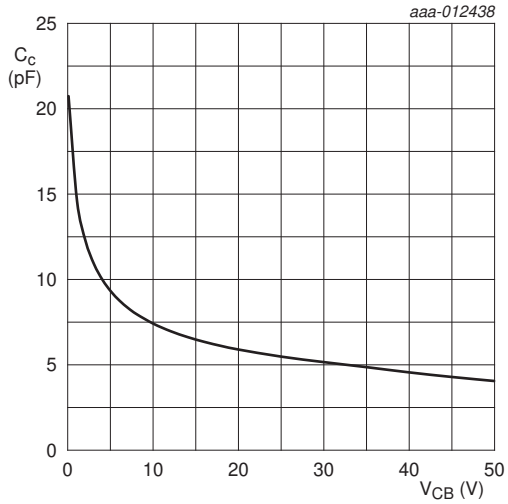
(3) T_{amb} = 100 °C

Fig 21. PDTD123EU: Off-state input voltage as a function of collector current; typical values



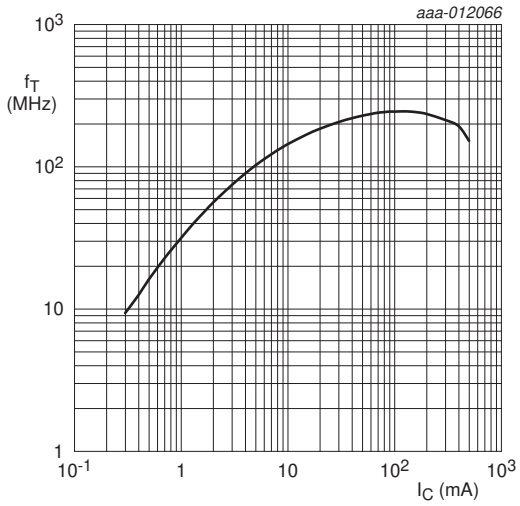
T_{amb} = 25 °C

Fig 22. PDTD123EU: Collector current as a function of collector-emitter voltage; typical values



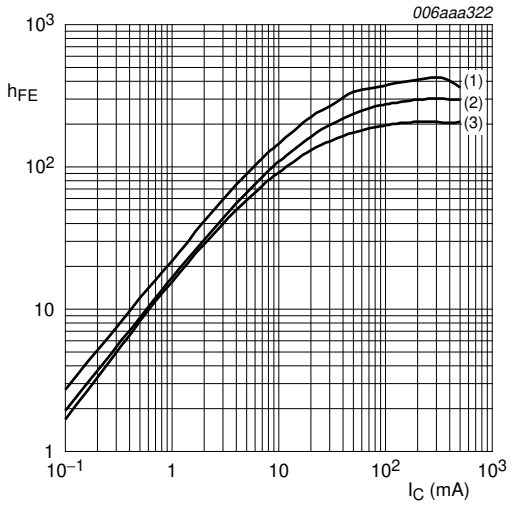
f = 1 MHz; T_{amb} = 25 °C

Fig 23. PDTD123EU: Collector capacitance as a function of collector-base voltage; typical values



V_{CE} = 5 V; T_{amb} = 25 °C

Fig 24. PDTD123EU: Transition frequency as a function of collector current; typical values of built-in transistor



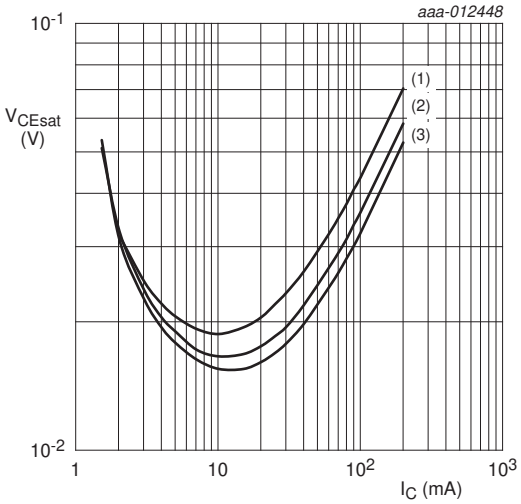
V_{CE} = 5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 25. PDTD123YU: DC current gain as a function of collector current; typical values



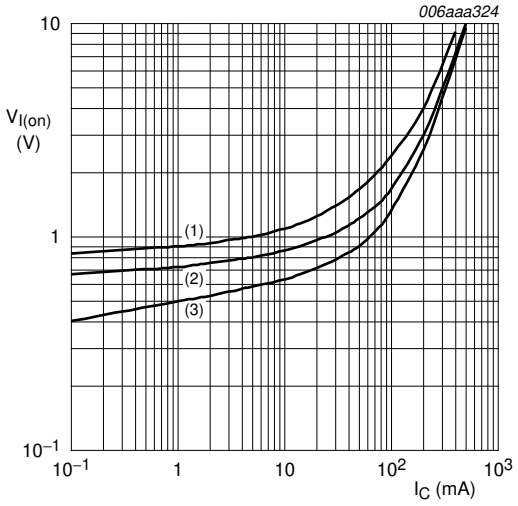
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 26. PDTD123YU: Collector-emitter saturation voltage as a function of collector current; typical values



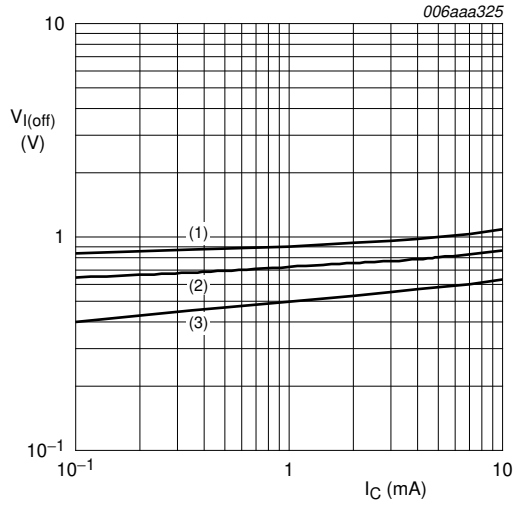
V_{CE} = 0.3 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 27. PDTD123YU: On-state input voltage as a function of collector current; typical values



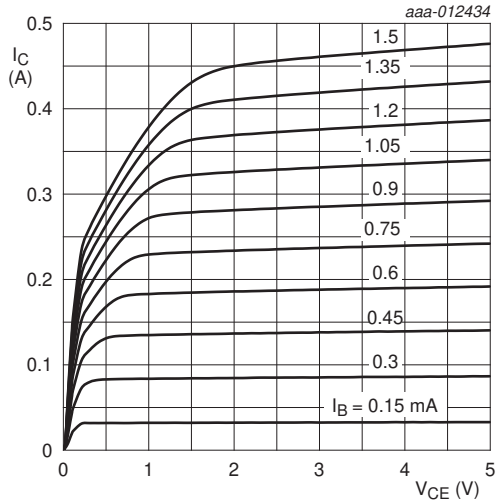
V_{CE} = 5 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

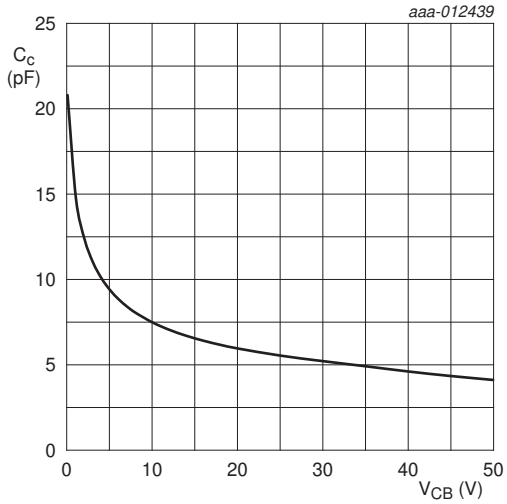
(3) T_{amb} = 100 °C

Fig 28. PDTD123YU: Off-state input voltage as a function of collector current; typical values



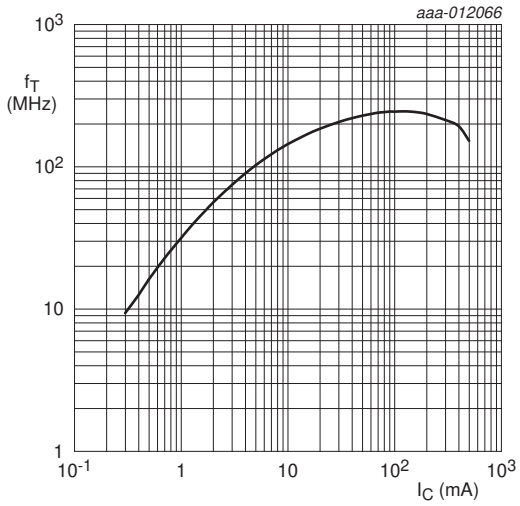
T_{amb} = 25 °C

Fig 29. PDTD123YU: Collector current as a function of collector-emitter voltage; typical values



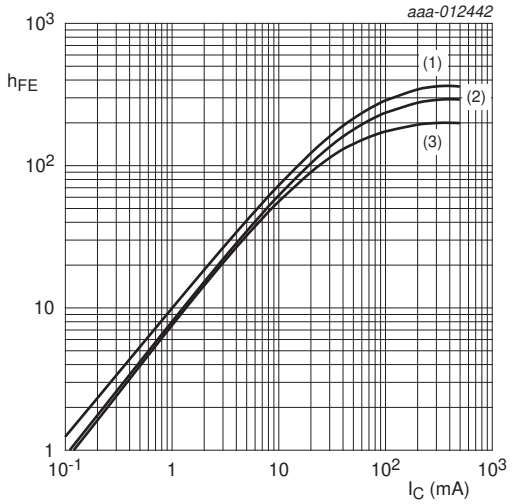
f = 1 MHz; T_{amb} = 25 °C

Fig 30. PDTD123YU: Collector capacitance as a function of collector-base voltage; typical values



V_{CE} = 5 V; T_{amb} = 25 °C

Fig 31. PDTD123YU: Transition frequency as a function of collector current; typical values of built-in transistor



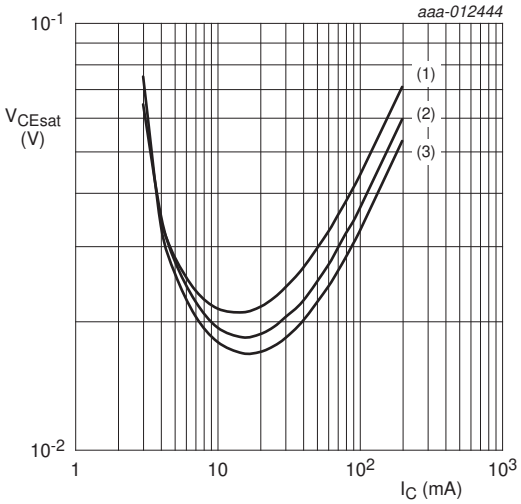
V_{CE} = 5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 32. PDTD143EU: DC current gain as a function of collector current; typical values



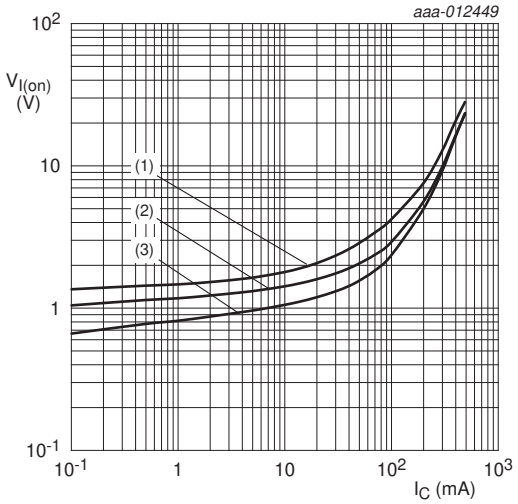
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 33. PDTD143EU: Collector-emitter saturation voltage as a function of collector current; typical values



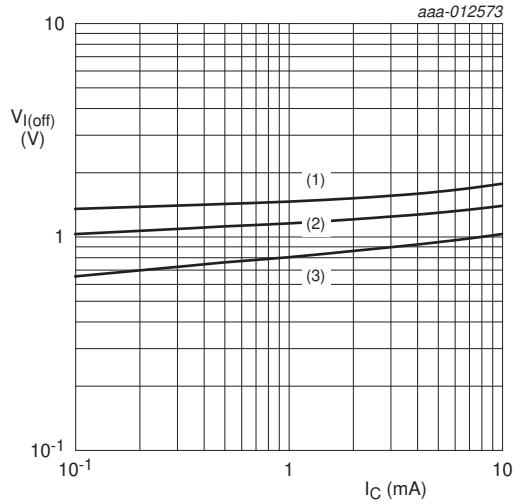
V_{CE} = 0.3 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 34. PDTD143EU: On-state input voltage as a function of collector current; typical values



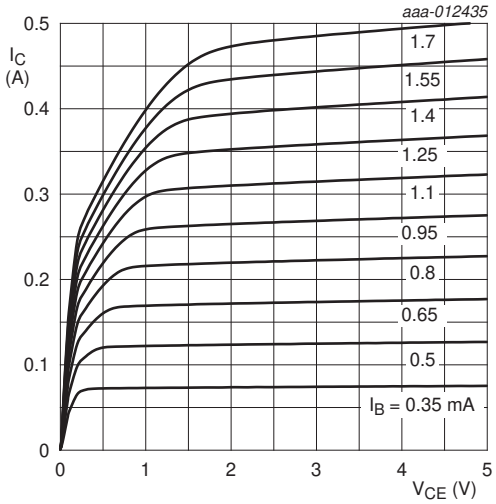
V_{CE} = 5 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

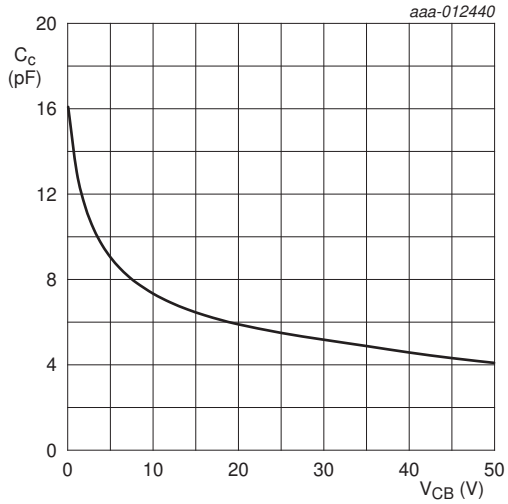
(3) T_{amb} = 100 °C

Fig 35. PDTD143EU: Off-state input voltage as a function of collector current; typical values



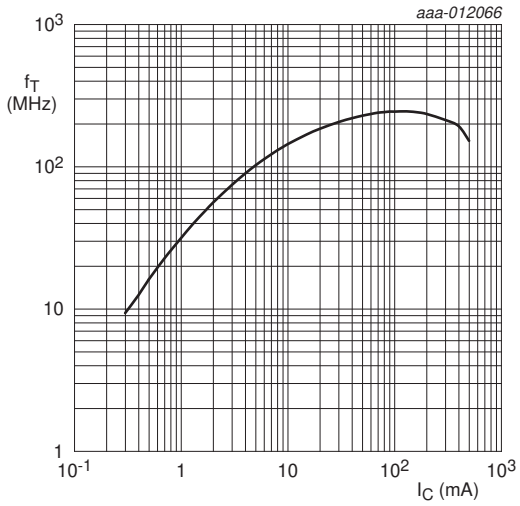
T_{amb} = 25 °C

Fig 36. PDTD143EU: Collector current as a function of collector-emitter voltage; typical values



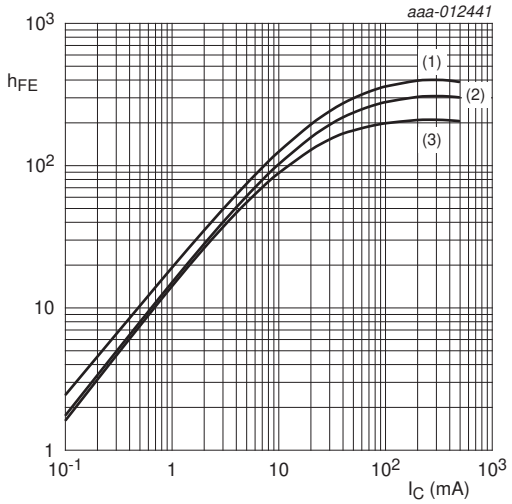
f = 1 MHz; T_{amb} = 25 °C

Fig 37. PDTD143EU: Collector capacitance as a function of collector-base voltage; typical values



V_{CE} = 5 V; T_{amb} = 25 °C

Fig 38. PDTD143EU: Transition frequency as a function of collector current; typical values of built-in transistor



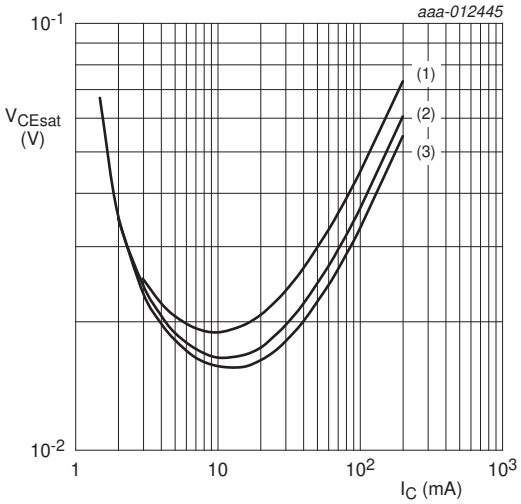
V_{CE} = 5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 39. PDTD143XU: DC current gain as a function of collector current; typical values



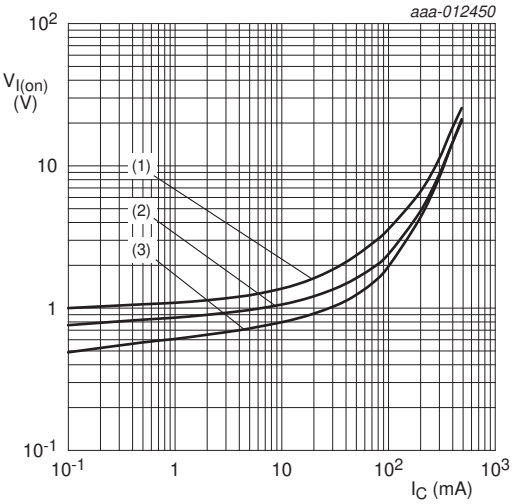
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 40. PDTD143XU: Collector-emitter saturation voltage as a function of collector current; typical values



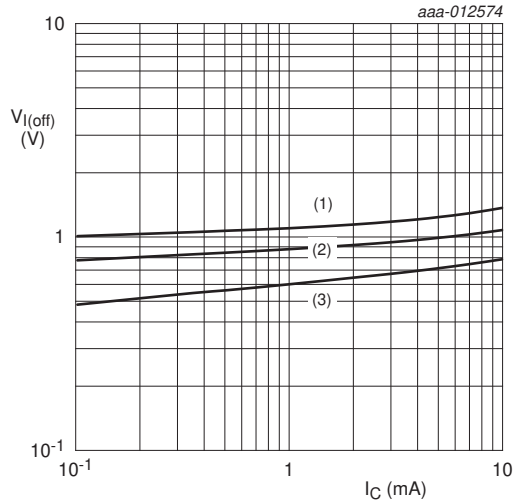
V_{CE} = 0.3 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 41. PDTD143XU: On-state input voltage as a function of collector current; typical values



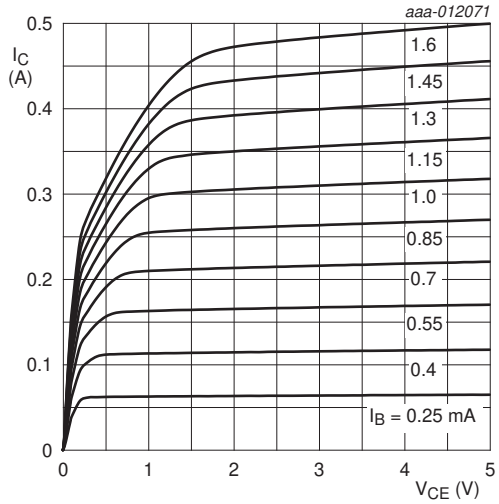
V_{CE} = 5 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

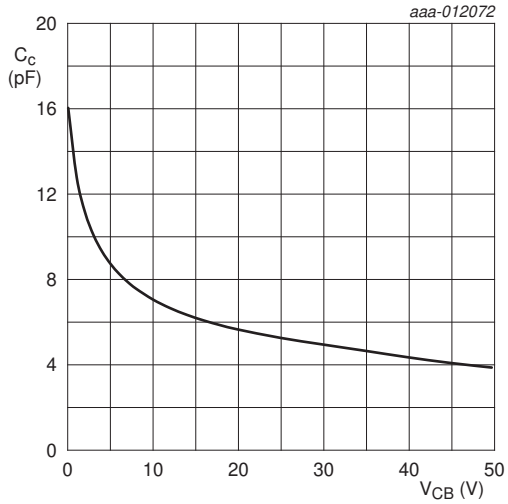
(3) T_{amb} = 100 °C

Fig 42. PDTD143XU: Off-state input voltage as a function of collector current; typical values



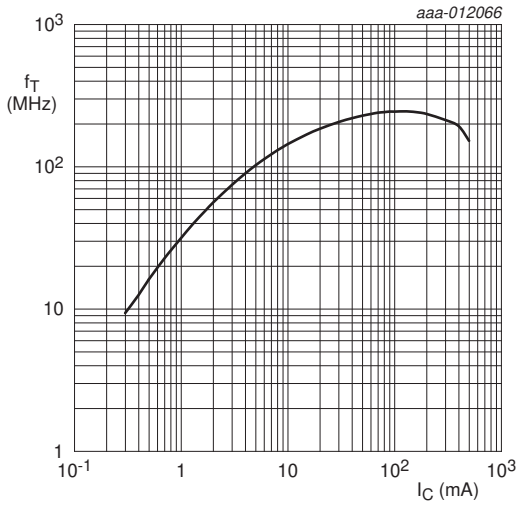
T_{amb} = 25 °C

Fig 43. PDTD143XU: Collector current as a function of collector-emitter voltage; typical values



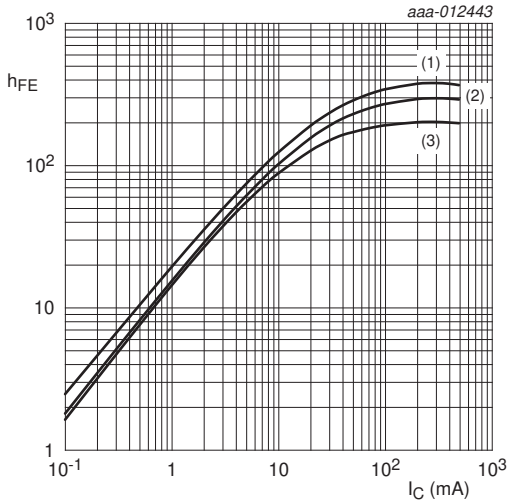
f = 1 MHz; T_{amb} = 25 °C

Fig 44. PDTD143XU: Collector capacitance as a function of collector-base voltage; typical values



V_{CE} = 5 V; T_{amb} = 25 °C

Fig 45. PDTD143XU: Transition frequency as a function of collector current; typical values of built-in transistor



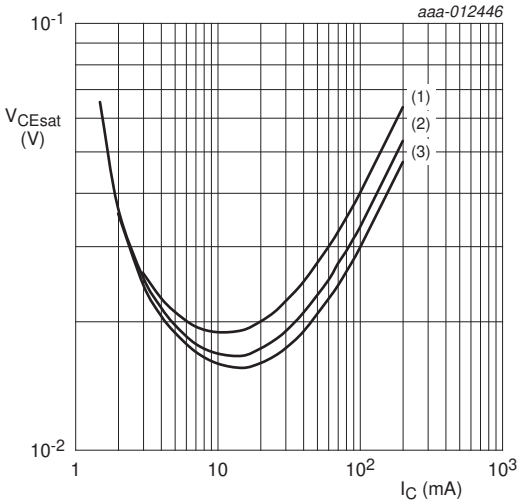
V_{CE} = 5 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 46. PDTD114EU: DC current gain as a function of collector current; typical values



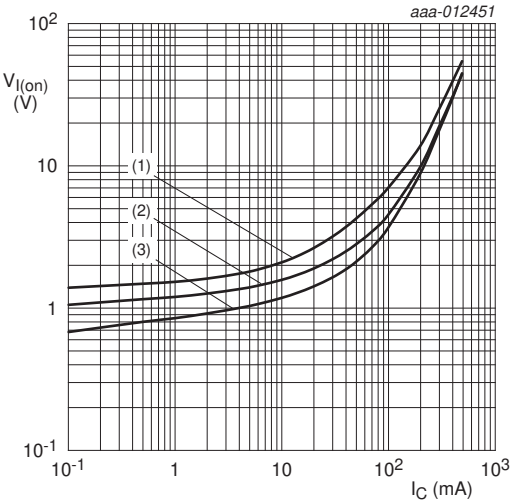
I_C/I_B = 20

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = −40 °C

Fig 47. PDTD114EU: Collector-emitter saturation voltage as a function of collector current; typical values



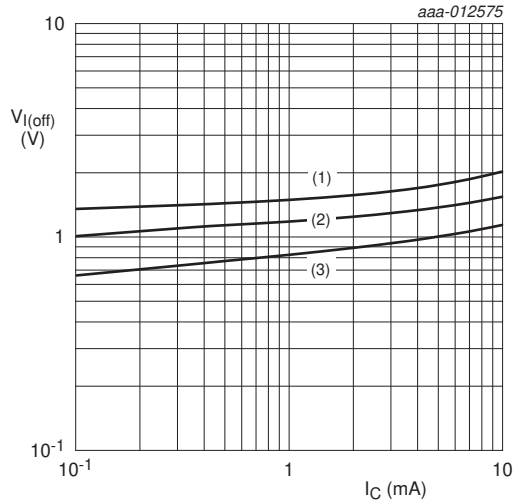
V_{CE} = 0.3 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 48. PDTD114EU: On-state input voltage as a function of collector current; typical values



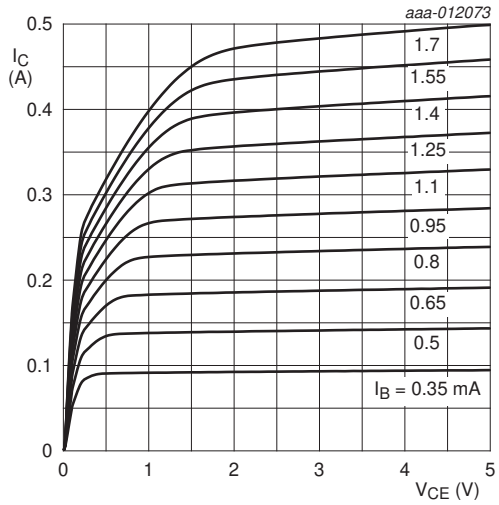
V_{CE} = 5 V

(1) T_{amb} = −40 °C

(2) T_{amb} = 25 °C

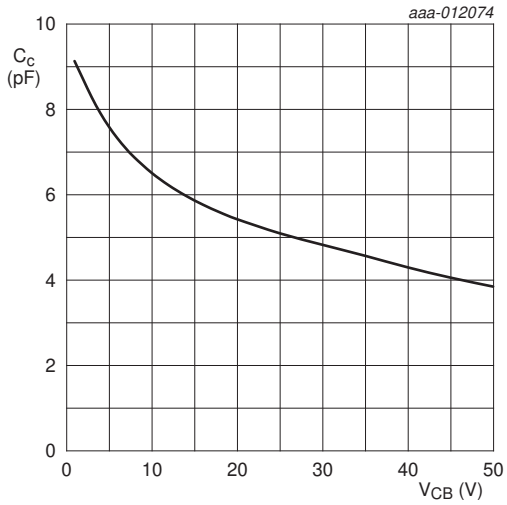
(3) T_{amb} = 100 °C

Fig 49. PDTD114EU: Off-state input voltage as a function of collector current; typical values



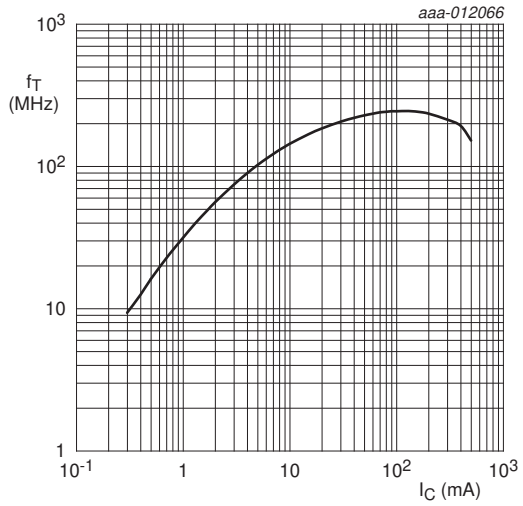
T_{amb} = 25 °C

Fig 50. PDTD114EU: Collector current as a function of collector-emitter voltage; typical values



f = 1 MHz; T_{amb} = 25 °C

Fig 51. PDTD114EU: Collector capacitance as a function of collector-base voltage; typical values



V_{CE} = 5 V; T_{amb} = 25 °C

Fig 52. PDTD114EU: Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

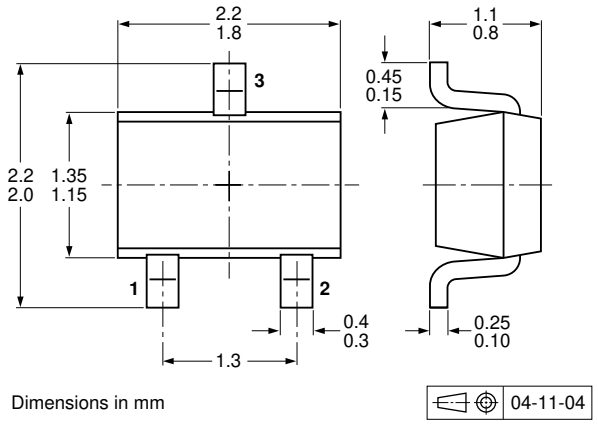
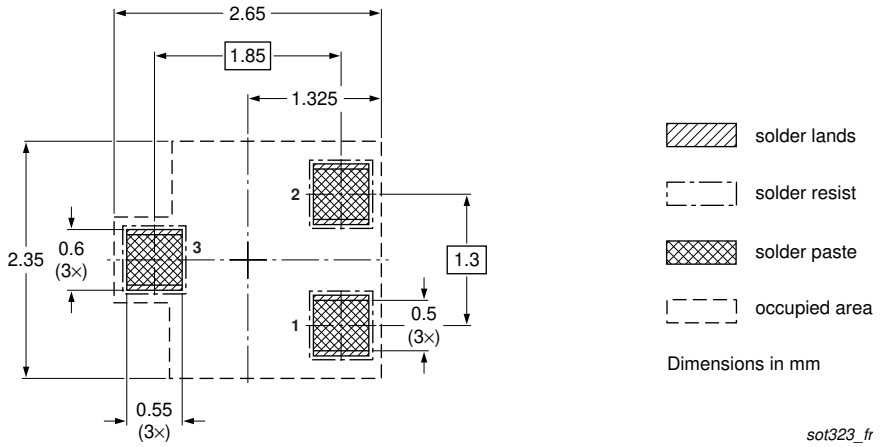


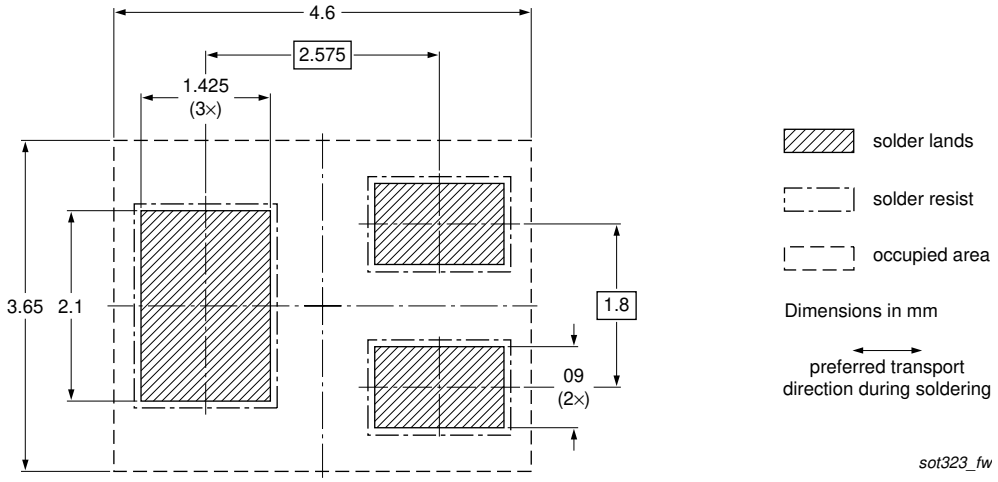
Fig 53. Package outline PDTD1xxxU series (SOT323/SC-70)

10. Soldering



Dimensions in mm

Fig 54. Reflow soldering footprint PDTD1xxxU series (SOT323/SC-70)



Dimensions in mm

Fig 55. Wave soldering footprint PDTD1xxxU series (SOT323/SC-70)

11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTD1XXXU_SER v.1	20140513	Product data sheet	-	-